Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1096	349/187 and @ad<"20031117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
L2	493	349/187 and @ad<"20031117" and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:34
L3	508	349/187 and @ad<"20031117" and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:36
L4	605	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:41
L5	104	"349"/\$.ccls. and @ad<"20031117" and mask\$4 and gate and data and pad and pixel and (thin adj film adj transistor adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:42
S48	927	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:31
S49	963	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S50	27	cutting-off adj plate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:37

S51	4883	expos\$4 near10 pad near10 etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:38
S52	237	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 11:15

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S53	239	("1954691"	L "2851408"	"2867541"	US-PGPUB;	OR	OFF	2005/05/19 16:28
333	233	•	"3070441"	"3108904"	USPAT;		0	2000,00,10 10:20
		"3259782"	"3314871"	"3360450"	USOCR			
		"3525679"	"3554889"	"3665241"				
		"3675063"	"3755704"	"3789471"				
		"3808048"	"3812559"	"3855499"				
		"3898146"	"3947716"	"3970887"				
		"3998678"	"4008412"	"4075535"				
		"4084942"	"4139773"	"4141405"				
		"4143292"	"4164680"	"4168213"				
		"4178531"	"4307507"	"4350926"				
		"4482447"	"4498952"	"4507562"				
		"4512912"	"4513308"	"4540983"				
		"4542038"	"4578614"	"4588921"				
		"4594527"	"4633131"	"4647400"				
		"4663559"	"4684353"	"4684540"				
		"4685996"	"4687825"	"4687938" İ				
		"4710765"	"4721885"	"4728851"				
		"4758449"	"4763187"	"4780684"				
		"4788472"	 "4816717"	"4818914"				
		"4822466"	"4827177"	"4835438" [
		"4851254"		"4857161"				
			"4874981"	"4882659"				
		"4889690"	"4892757"	"4899081"				
		"4900584"		"4923421"				
		"4926056"		"4940916"				
		"4943343"	"4956202"	"4956574"				
		"4964946"	"4987007"	"4990416"				
		"4990766"	"4994205"	"5007873"				
		"5015912"	, "5019003"	"5036247"				
		"5038070"	"5043715"	"5054046"				
, !		"5054047"	"5055077"	"5055744"				
		"5057047"	"5063323"	"5063327"				
		"5064396"	"5066883"	"5075591"				
		"5075595"	"5075596"	"5079476"				
		"5085958"	"5089292"	"5089742"				
		"5089812"	"5090932"	"5098737"				
		"5101137"	"5101288"	"5103144"				
		"5103145"	"5117267"	"5117299"				
		"5119386"	"5123039"	"5124072"	,			
		1	"5126287"					
		i	"5132676").					
		, .	•	"5140219"				
	'		"5141460"					
		,	"5142390"					
		1	"5148461"	· -				
			"5151061"	•				
			"5155420"					
		l .	"5157309"					
		!	"5173634"					
		1	"5180951"					
			"5186670"			1		
	ļ	I.	"5192240"	· -				
			"5199918"			•	1	
			"5203731"					
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C:\Docu	ments and Set	ttings\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	"5210462" "5214346" 	STWOTKSPACES	s\10713198[cuttin	g_off_plate_	dry_etchin	g].wsp
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1	I	· "5714416"	I "577N775"		I	1	,	'

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S54	24	(expos\$4 near10 pad near10 (dry adj etch\$4)) and gate and data and semiconductor and pixel and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 16:29
S55	94	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S56	2	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and cut\$4-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S57	998	349/143	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S58	367	349/150	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S59	1653	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:25
S60	357	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S61	73	349/150 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33

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S62	131	349/152 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S63	114	349/143 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S65	84	349/143 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S67	66	349/152 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S69	291	349/43 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:39
S70	111	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:08
S71	9	(expos\$4 near10 pad near10 etch\$4) and gate and data and semiconductor and pixel and mask\$4 and ((mask cutting-off) near10 metal) and ((three "3") adj mask\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 12:54
S72	1857216	(dry adj etch\$4) nea10 insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:11

S73	4990943	S72 (liquid adh crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S74	2348219	S72 (liquid adh crystal) and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S75	150088	(dry adj etch\$4) nea10 insulat\$4 near10 expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:15
S76	11537	S75 and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:12
S77	2992	(S75 near10 remov\$4)and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S78	833	(S75 near10 remov\$4)and (liquid adj crystal) and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S79	228	(S75 near10 remov\$4)and (liquid adj crystal) and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:14
S80	1281	(dry adj etch\$4) near10 insulat\$4 near10 expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:15

S81	40	(dry adj etch\$4) near10 insulat\$4 near10 expos\$4 and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:16
S82	401	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S83	155	349/152 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S84	96	349/143 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S85	86	349/150 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S86	80	349/152 and pad and expos\$4 and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S88	146	349/143 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S89	425	349/43 and pad and expos\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21

S90	1193 349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
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